

NANOPOWER

Relaxation rate in ultra thin silicon membrane

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CREATING A DIMENSION OF INFINITE POSSIBILITIES















Motivation



A. Balandin et al, PRB 58(1998) 1544

Effect of native oxide on dispersion relation

Heat transport in nm scale







30 nm

Motivation



Outline

♣ Theory:

- Elastic continuum model
- Equation of motion
- Dispersion relation
- ♣ Relaxation rate & Thermal conductivity:
 - Scattering mechanisms: Umklapp & Normal
 - Relaxation rate for U-processes
 - Thermal conductivity
- ✤ Numerical results: discussion
- Conclusions

Theory

Elastic continuum theory

- Stress-strain relationship
- "Macroscopic model" i.e. continuum-based and isotropic
- Well-suited for nanoscale confinement studies



Motion equation :

$$\partial^2 U/\partial t^2 = S_T^2 \nabla^2 U + (S_L^2 - S_T^2) \nabla (\nabla \cdot U)$$

$$S_T = \sqrt{(\lambda + 2\mu)/\rho}$$
$$S_L = \sqrt{\mu/\rho}$$

U = Vector amplitude of displacement

 ρ = Density

 λ, μ = Lamé constants

 S_T , S_L = Transversal and longitudinal sound speed

Single Layer Solutions



J.L. Rose, Ultrasonic waves in solid media, Cambridge University press, UK, 2004

Three layer Solutions $T_{iz}|_{z=surface} = 0$



System symmetry \rightarrow 6 linear equations, i.e., 6x6 matrix.

 $DW^{\mathrm{x(z)}}$: Dilatational Waves solutions en x (z) components.

 $FW^{x(z)}$: Flexural Waves solutions en x (z) components.

- B. C. : Boundary Conditions.
- C. C. : Continuity Conditions.

L. Donetti, F. Gámiz, J. B. Róldan and A. Godoy, J Appl. Phys. 100 (2006), 013701

Dispersion Relation & Group velocity



DW: Dilatational Waves FW: Flexural Waves SW: Shear Waves 8

 $S_1 = 8.440 \text{ kms}^{-1}$, $S_T = 5.845 \text{ kms}^{-1}$, a = 10 nm

Experimental Results & Theory



Dispersion of Confined Acoustic Phonons in Ultra-Thin Silicon Membranes, J. Cuffe et al., in preparation

Si v/s SiO₂-Si-SiO₂



large $q_{//}$ & high order modes

×

a=28.5 nm b=1.6 nm	A } a	a=29.42 nm

Experimental Results & Theory

30 nm Si membrane



Other systems



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Scattering Mechanisms



Consequence of anharmonicity \rightarrow Phonon-phonon interaction \rightarrow Finite phonon lifetime Possibilities:

1. Annihilation of two phonons and creation of a third phonon.

2. Annihilation of one phonon and creation of two phonons

Selection Rules: U & N-Process



Relaxation Rate & Thermal conductivity

$$\frac{1}{\tau_{U;q,s}} = \frac{\pi \gamma^2 \hbar}{\rho N_0 \Omega \overline{\nu}^2} \sum_{q's',q''s'',G} \omega_{q,s} \omega_{q',s'} \omega_{q'',s''} (n_{q's'} - n_{q''s''}) \delta(\omega_{qs} + \omega_{q's'} - \omega_{q''s''}) \delta_{q+q',q''+G}$$

Phonon average group velocity

$$\overline{v}_{s} = \sum_{q} v_{qs} n_{qs} / \sum_{q} n_{qs} \qquad \kappa = \frac{1}{3} \sum_{q,s} v_{q,s}^{2} \tau_{eff} C_{V}$$

$$\kappa = \frac{\hbar \rho \overline{v}^{2}}{3\pi \gamma^{2} k_{B} T^{2}} \sum_{qs} v_{qs}^{2} \omega_{qs}^{2} n_{qs} (n_{qs} + 1) \left\{ \sum_{q's';q''s'';G} (n_{q's'} - n_{q''s''}) \omega_{qs} \omega_{q's''} \omega_{q''s''} \delta(\Delta \omega) \delta_{q+q'-q'',G} \right\}^{-1}$$

More Branches \rightarrow More interactions \rightarrow Decrease thermal conductivity. Change of group velocity (v_{qs}) \rightarrow Change in thermal conductivity

A. AlShaikhi and G.P. Srivastava, Phys. Rev. B, 76 (2007), pp. 195205-1.

B. G. P. Srivastava, "The Physics of Phonons", Taylor & Francis Group, NY, 1990.

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Results: Relaxation Rates



The modification of dispersion and group velocity lead to increase of relaxation rate compared with the bulk (left).

The decrease in frequency of 3-layer membrane lead to decrease on relaxation rate compared with 1-layer membrane (right).

Results: Thermal Conductivity

Intrinsic thermal conductivity



The numerical calculations predict a strong decrease of the thermal conductivity of a 1-layer membranes.

Summary



Conclusions

- ✤ Hybridization of sagittal waves.
- Group velocity dependence on $q_{//}$: $v_g(q_{//})$.
- Oxide effect: decrease of frequency for large $q_{//}$ \rightarrow Decrease in relaxation rate.
- The change in dispersion relation and the emergence of more branches implies an increase of phonon-phonon interactions. This causes an increase in relaxation rates and a corresponding decrease in the thermal conductivity.

Future Work

Phononic structures



an epoxy matrix (sagittal waves)



Y. Pennec et al, surface science reports 65(2010), pp 229-291





ωa/2πC

